

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	@ad<="20030922" and 'interconnection' and 'SiOC' with 'SiC' and 'USG' and 'organosilicate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:09
L2	0	@ad<="20030922" and 'interconnection' and 'SiOC' with 'SiC' and 'USG' and 'low k'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:04
L4	20	@ad<="20030922" and 'etch stop' same 'SiOC' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:26
L5	3	@ad<="20030922" and 'etch stop' same 'SiCON' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:05
L6	1	@ad<="20030922" and 'etch stop' same 'SiCON' same 'SiC' same 'SiCO'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:05
L7	9	@ad<="20030922" and 'etch stop' same 'SiCO' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:27
L8	1	@ad<="20030922" and 'etch stop' same 'SiOCN' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:28
L9	2	@ad<="20030922" and 'hard mask' same 'SiOCN' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:30
L10	2	@ad<="20030922" and 'hard mask' same 'SiCON' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:31
L11	31	@ad<="20030922" and 'hard mask' same ('SiCO' or 'SiOC') with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:47

L12	8	("6140224") or ("6339025") or ("5559367") or ("6147007").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 11:49
L13	2	("6147009").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 11:49
L14	2	@ad<="20030922" and 'substrate' and 'interconnection' and 'SiOC' and 'USG' and 'low k' and 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:11
L15	0	@ad<="20030922" and 'semiconductor substrate' and 'hard mask' with 'SiOC' and 'USG' and 'low k' and 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:12
L16	0	@ad<="20030922" and 'hard mask' with 'SiOC' and 'USG' and 'low k' and 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:13
L17	0	@ad<="20030922" and 'etch stop' with 'SiOC' and 'USG' and 'low k' and 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:13
L18	3	@ad<="20030922" and 'etch stop' with 'SiCO' and 'USG' and 'low k' and 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 13:13
L19	0	@ad<="20030922" and 'hard mask' with 'SiCO' and 'USG' and 'low k' and 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:13
L20	109	@ad<="20030922" and 'dielectric constant' with 'Black Diamond'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 13:13
S1	1705	@ad<="20020607" and (257/773).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:42

S2	4488	@ad<="20020607" and (438/622-624).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:09
S3	557	@ad<="20020607" and (438/629).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:42
S4	1623	@ad<="20020607" and (438/637).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:42
S5	545	@ad<="20020607" and (438/631).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:42
S6	0	@ad<="20020607" and 'interconnection' and 'IDL' with 'SiOC' and 'insulating' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:22
S7	0	@ad<="20020607" and 'interconnection' and 'IDL' same 'SiOC' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/10 10:43
S8	0	@ad<="20020607" and 'interconnection' and 'SiOC' same 'SiC' same 'USG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:03
S9	23	@ad<="20020607" and 'interconnection' and 'SiOC' same 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:34
S10	1	@ad<="20020607" and 'dielectric' same 'SiOC' same 'undoped silicate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/10 10:50
S11	28	@ad<="20020607" and 'dielectric' same 'SiOC' same 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 09:57
S12	2	@ad<="20020607" and 'dielectric' same 'SiOC' same 'SiC' same 'PSG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/10 12:12

S13	1	@ad<="20020607" and 'dielectric' same 'SiOC' same 'SiC' same 'USG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/10 12:13
S14	0	@ad<="20020607" and 'interconnection' and 'SiOC' same 'USG' same 'SiN'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/26 17:40
S15	26	@ad<="20020607" and 'interconnection' and 'SiOC' same 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/26 17:39
S16	2	@ad<="20020607" and 'interconnection' and 'SiOC' and 'USG' and 'SiN'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/26 17:45
S17	15	@ad<="20020607" and 'interconnection' and 'SiOC' same 'SiC' and 'SiN'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/26 17:45
S18	28	@ad<="20020607" and 'low k' same 'silicon oxide' same 'SiN'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/09 14:34
S19	969	@ad<="20020607" and (257/750).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:43
S20	2856	@ad<="20020607" and (257/758-760).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:44
S21	1737	@ad<="20020607" and (257/773).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:45
S22	4552	@ad<="20020607" and (438/622-624).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:47
S23	564	@ad<="20020607" and (438/629).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:47

S24	1664	@ad<="20020607" and (438/637).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:49
S25	548	@ad<="20020607" and (438/631).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/27 11:49
S26	2	"20030227087"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/09 13:41
S27	86	@ad<="20020607" and 'hard mask' same 'SiN' with 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 12:22
S28	39	@ad<="20020607" and 'hard mask' same 'SiN' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/09 14:36
S29	18	@ad<="20020607" and 'low k' same 'hard mask' same 'SiN' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/09 14:36
S30	2	@ad<="20020607" and 'MSQ' same 'hard mask' same 'SiN' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:43
S31	5	@ad<="20020607" and 'MSQ' same 'SiN' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/09 14:59
S32	19	@ad<="20020607" and 'hard mask' same 'SiC' with 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 12:23
S33	2	@ad<="20020607" and 'hard mask' same 'SiC' with 'TEOS'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 13:41
S34	17	@ad<="20020607" and 'etch stop' with 'SiC' with "SiO.sub.2"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 13:42

S35	2	@ad<="20020607" and 'MSQ' same 'etch stop' with 'SiC' with "SiO.sub.2"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 13:42
S36	4	"6677183"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 15:38
S37	649	@ad<="20020607" and 'interconnection' same 'tungsten' with 'copper' same' low k' same 'etch stop' with 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:25
S38	31	@ad<="20020607" and 'interconnection' same 'tungsten plug' with 'copper' same' low k' same 'etch stop' with 'SiC' same 'USG'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:30
S39	90	@ad<="20020607" and 'tungsten copper' same 'interconnection'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:32
S40	0	@ad<="20020607" and 'tungsten copper' same 'interconnection' and 'low k' and 'SiC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:32
S41	17	@ad<="20020607" and 'tungsten copper' same 'interconnection' and 'etch stop'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:32
S42	0	@ad<="20020607" and 'interconnection' and 'USG' same 'SiC' same 'low k'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:35
S43	7	@ad<="20020607" and 'interconnection' and 'USG' and 'SiC' and 'low k'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:35
S44	12	@ad<="20030922" and 'interconnection' and 'USG' and 'SiC' and 'low k'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:35
S45	1	"6312793".PN.	USPAT	OR	OFF	2004/10/31 08:39
S46	1	"6303523".PN.	USPAT	OR	OFF	2004/10/31 08:40
S47	1	"6238751".PN.	USPAT	OR	OFF	2004/10/31 08:40
S48	1	"6147009".PN.	USPAT	OR	OFF	2004/10/31 08:40

S49	1	"6072227".PN.	USPAT	OR	OFF	2004/10/31 08:40
S50	1	"6054379".PN.	USPAT	OR	OFF	2004/10/31 08:40
S51	1	"6001747".PN.	USPAT	OR	OFF	2004/10/31 08:41
S52	1	"5989998".PN.	USPAT	OR	OFF	2004/10/31 08:41
S53	2	@ad<="20020607" and 'USG' same 'hard mask' same 'low dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:46
S54	270	@ad<="20020607" and 'dielectric' same 'hard mask' same 'low dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:58
S55	24	@ad<="20020607" and 'interconnection' same 'dielectric' same 'hard mask' same 'low dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:53
S56	4	(("6465867") or ("6016000")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/31 08:55
S57	2	"20010045651"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:55
S58	190	@ad<="20020607" and 'dielectric' same 'SiC' same 'low dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:59
S59	56	@ad<="20020607" and 'dielectric' same 'SiC' same 'low dielectric' same 'barrier'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 07:19
S60	34	@ad<="20020607" and 'dielectric' same 'SiC' same 'low-k' same 'barrier'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/31 08:59
S61	2447	@ad<="20030922" and (257/750-752).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:03
S62	1757	@ad<="20030922" and (257/753-756).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:05

S63	3767	@ad<="20030922" and (257/757-760).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:06
S64	1886	@ad<="20030922" and (257/773).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:07
S65	126	@ad<="20030922" and 'dielectric constant' with 'SiOC'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:15
S66	7	@ad<="20030922" and 'conductive plug' with 'Cu' with 'W' with 'silicide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:31
S67	138	@ad<="20030922" and 'conductive' with 'Cu' with 'W' with 'silicide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:18
S68	1	@ad<="20030922" and 'interconnect' same 'conductive' with 'Cu' with 'W' with 'silicide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:19
S69	12	@ad<="20030922" and 'interconnection' same 'conductive' with 'Cu' with 'W' with 'silicide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:19
S70	36	@ad<="20030922" and 'interconnection' same 'substrate' with 'Silicon' with 'silicon germanium'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 09:32